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- a first doped region of type one, doped in the well of type two;
- a third doped region of type one, doped in the well of type one, not touching the first doped region of type two;
- a third doped region of type two, doped in the well of type two, directly touching the first doped region of type one;
- a first conductive material, provided on the well of type one and the well of type two but not on the first doped region of type one and the first doped region of type two; and
- a second conductive layer, provided on the well of type two but not on the first doped region of type one;
- wherein the substrate comprises no isolating material provided in a current path formed by the first doped region of type two, the well of type one, the well of type two and the first doped region of type one in a sequence.
2. The semiconductor device of claim 1, wherein no silicide is provided on at least part of the well of type one adjacent to the first doped region of type two, and at least part of the first doped region of type two adjacent to the well of type one.
3. The semiconductor device of claim 1, wherein the substrate further comprising:
- a second doped region of type one, provided in the well of type two; and
- a second doped region of type two, provided in the well of type two;
- wherein the second doped region of type two and the second doped region of type one are provided between the first doped region of type one and first doped region of type two;
- wherein the first conductive material is provided on a region between the first doped region of type two and the second doped region of type two;
- wherein the second conductive material is provided on a region between the first doped region of type one and the second doped region of type one.
4. The semiconductor device of claim 1, wherein the type one is N type and the type two is P type.
5. The semiconductor device of claim 1, wherein the type one is P type and the type two is N type.
6. The semiconductor device of claim 1, wherein no silicide is provided on at least part of the well of type one adjacent to the third doped region of type one, and at least part of the third doped region of type one adjacent to the well of type one.
7. A semiconductor device, comprising:
- a substrate, comprising:
- a well of type one;
- a first doped region of type two, provided in the well of type one;
- a well of type two, adjacent to the well of type one;

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- a first doped region of type one, doped in the well of type two;
- a first conductive material, provided on the well of type one and the well of type two but not on the first doped region of type one and the first doped region of type two; and
- a second conductive layer, provided on the well of type two but not on the first doped region of type one;
- wherein the substrate comprises no isolating material provided in a current path formed by the first doped region of type two, the well of type one, the well of type two and the first doped region of type one.
8. The semiconductor device of claim 7, wherein the substrate further comprising:
- a second doped region of type one, provided in the well of type two; and
- a second doped region of type two, provided in the well of type two;
- wherein the second doped region of type two and the second doped region of type one are provided between the first doped region of type one and first doped region of type two;
- wherein the first conductive material is provided on a region between the first doped region of type two and the second doped region of type two;
- wherein the second conductive material is provided on a region between the first doped region of type one and the second doped region of type one.
9. A semiconductor device, comprising:
- a substrate, comprising:
- a well of type one;
- a first doped region of type two, provided in the well of type one;
- a well of type two, adjacent to the well of type one;
- a first doped region of type one, doped in the well of type two;
- a third doped region of type one, doped in the well of type one, not touching the first doped region of type two;
- a third doped region of type two, doped in the well of type two, touching the first doped region of type one;
- a first conductive material, provided on the well of type one and the well of type two but not on the first doped region of type one and the first doped region of type two; and
- a second conductive layer, provided on the well of type two but not on the first doped region of type one;
- wherein the substrate comprises no isolating material provided in a current path formed by the first doped region of type two, the well of type one, the well of type two and the first doped region of type one;
- wherein no silicide is provided on at least part of the well of type one adjacent to the third doped region of type one, and at least part of the third doped region of type one adjacent to the well of type one.

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